

CZ Wafer	Prime Polished Wafer	P-Type (100), 15~25 $\Omega\cdot\text{cm}$
Characteristics Items		Specification
General Characteristics	Growth Method	CZ
	Crystal Orientation/Tolerance	$\{100\} \pm 0.5^\circ$
	Conductive Type	P-Type
	Dopant	Boron
Electrical Characteristics	Resistivity	15~25 $\Omega\cdot\text{cm}$
	Radial Resistivity Gradient(RRG)	<5% (edge 6mm)
	Resistivity Striations	None
Chemical Characteristics	Oxygen Concentration	12.5~16.5 ppma
	Oxygen Radial Gradient(ORG)	<6%
	Carbon Concentration	$\cong 0.5$ ppma
Structural Characteristics	Oxygen Induced Stacking Fault(OISF)	<10 /cm ²
	Slip	None
	Dislocation	None
	Lineage	None
	Twin	None
	Swirl	None
Mechanical Characteristics	Diameter/Tolerance	150 $\pm$ 0.2 mm
	Primary Flat Orientation/Tolerance	$\{110\} \pm 1^\circ$
	Primary Flat Length/Tolerance	47.5 $\pm$ 2.5 mm ①
	Secondary Flat Location	None
	Secondary Flat Length/Tolerance	None
	Edge Profile	R-Type Per SEMI STD
	Thickness/Tolerance	625 $\pm$ 15 μm
	BOW	<30 μm
	WARP	<30 μm
	GBIR (TTV)	<4.0 μm
	GFLR (TIR)	<2.0 μm
	SBIR (STIR)	<1.0 μm (15mm $\times$ 15mm)
Front Surface Characteristics	Surface Finish	Polished
	Scratches Maximum Number	None
	Pits	None
	Haze	None
	Contamination, Particulate	<10 (@ $\geq 0.3\mu\text{m}$)
	Contamination, Area	None
	Edge Chips and Indents	None
	Cracks, Crow's Feet	None
	Craters	None
	Dimples	None
	Grooves	None
	Mounds	None
	Orange Peel	None

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P100B(15-25)T625FL475<110>

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Characteristics Items		Specification
Front Surface Characteristics	Saw Marks	None
	Edge Crown(for epitaxial layer)	/
	Surface Metals Concentration	<5.0E10 atoms/cm ² for each element:Na, Al, Cr, K, Fe, Ni, Cu, Zn
Back Surface Characteristics	Edge Chips	None
	Cracks, Crow's Feet	None
	Contamination, Area	None
	Saw Marks	None
	Back Etcher	Etched
	Extrinsic Gettering Treatment	Backside Damage
	Backseal	None
Others Characteristics		must meet SEMI STD except when noted

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